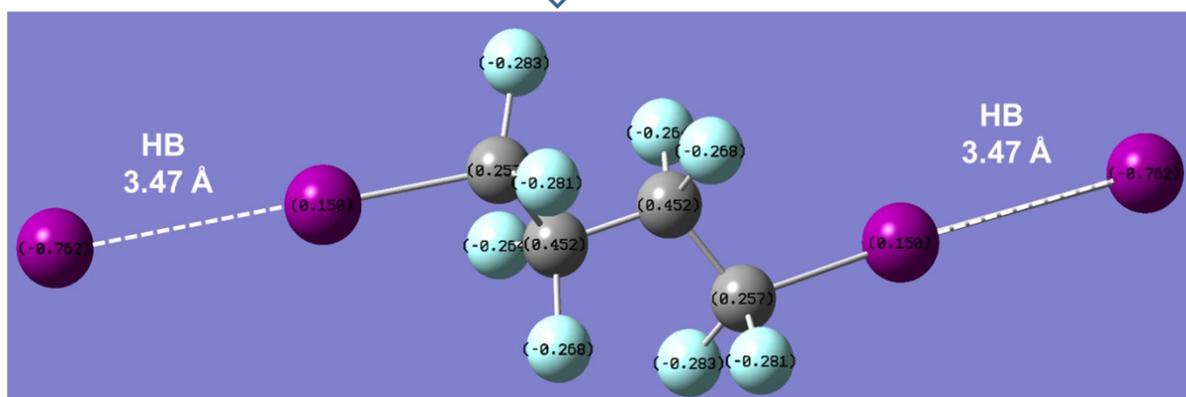
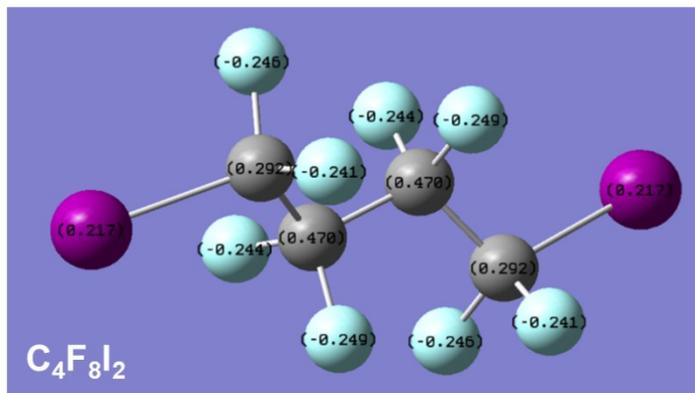


Supplementary Information

Halogen Bonding Reduces Intrinsic Traps and Enhances Charge Mobilities in Halide Perovskite Solar Cells

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a)



b)

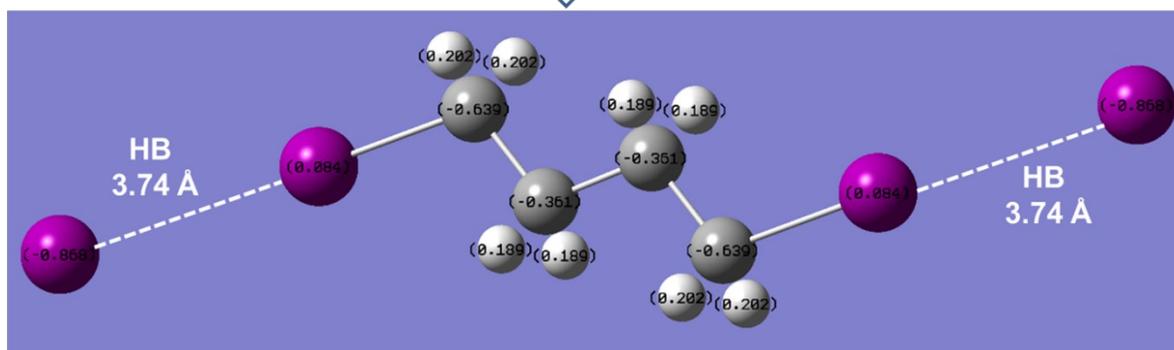
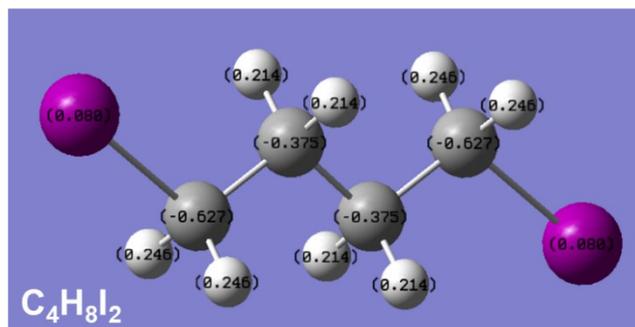


Figure S1. 3D chemical structures and halogen bonds with iodine anions illustrated by DFT calculations for (a) $C_4F_8I_2$ and (b) $C_4H_8I_2$ additives (purple: iodine, light blue: fluorene, grey: carbon, light grey: hydrogen). Dashed lines indicate the halogen bonds (HB) formed between the end group iodines with iodine anions in perovskite precursor solutions. Also included are the calculated Mulliken charges for iodines inside the additive molecules and the HB lengths.

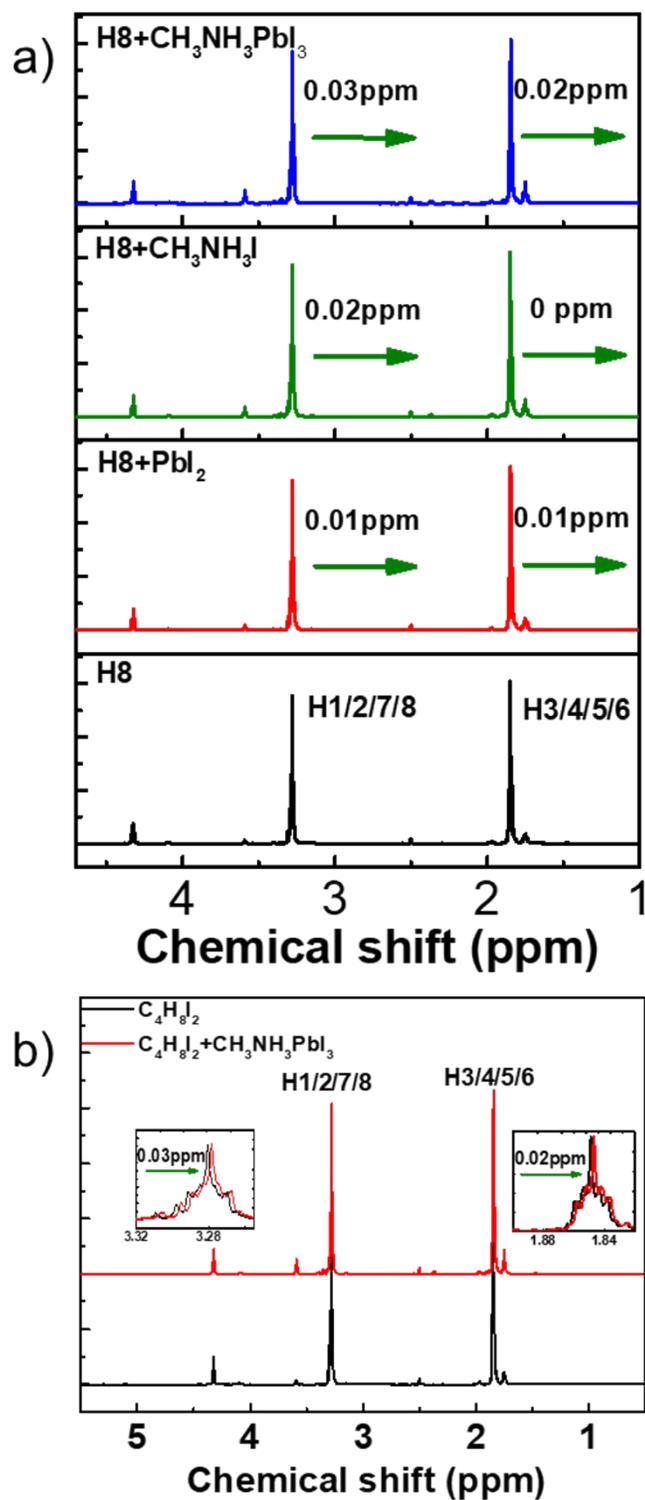


Figure S2. ^1H NMR spectra for pristine $\text{C}_4\text{H}_8\text{I}_2$ and $\text{C}_4\text{H}_8\text{I}_2$ -added solutions of PbI_2 , $\text{CH}_3\text{NH}_3\text{I}$, and $\text{PbI}_2/\text{CH}_3\text{NH}_3\text{I}$ mixture. Insets in (b): zoomed-in spectra at 3.28 and 1.85 ppm.

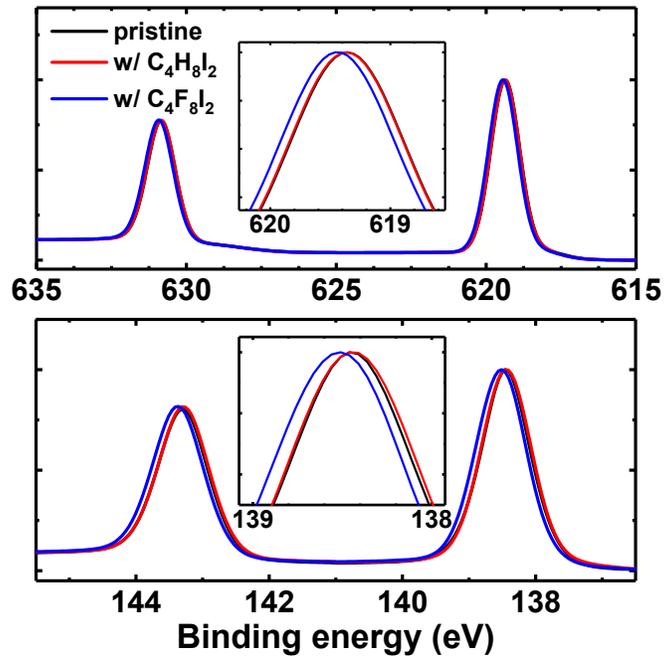


Figure S3. High-resolution X-ray photoelectron spectroscopy (XPS) of core level I 3d (upper panel) and Pb 4f (lower panel) measured on as-cast $\text{CH}_3\text{NH}_3\text{PbI}_3$ films. Inset: Zoomed-in spectra (normalized) of the 5/2 (I 3d) and 7/2 (Pb 4f) sub peaks to illustrate the upward shift of binding energy with additives.

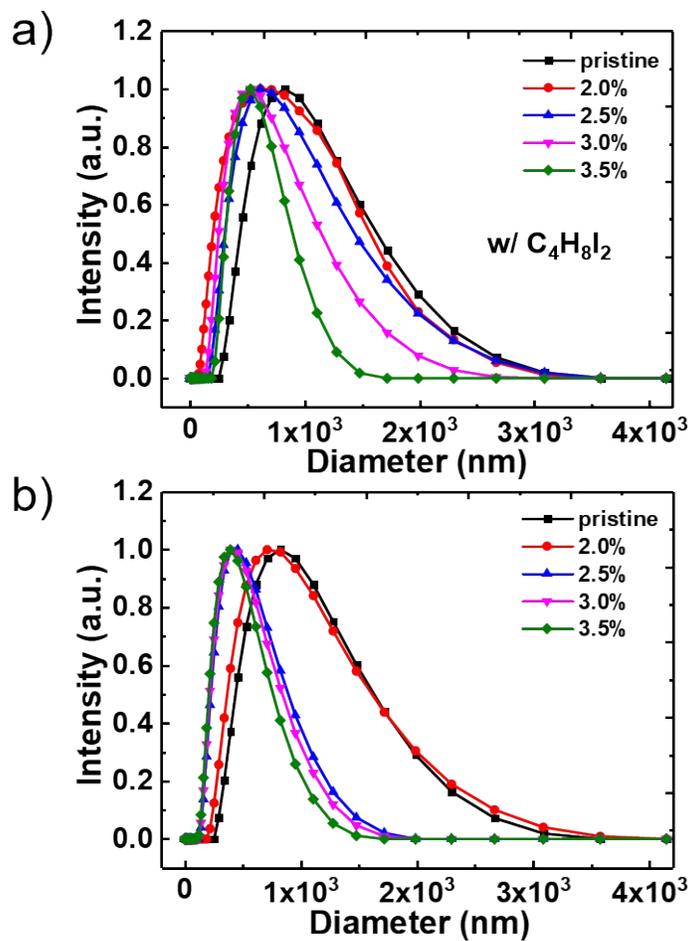


Figure S4. Diameter distribution for clusters in CH₃NH₃PbI₃ precursor solutions with various concentrations of (a) C₄H₈I₂ and (b) C₄F₈I₂ additives determined by dynamic light scattering.

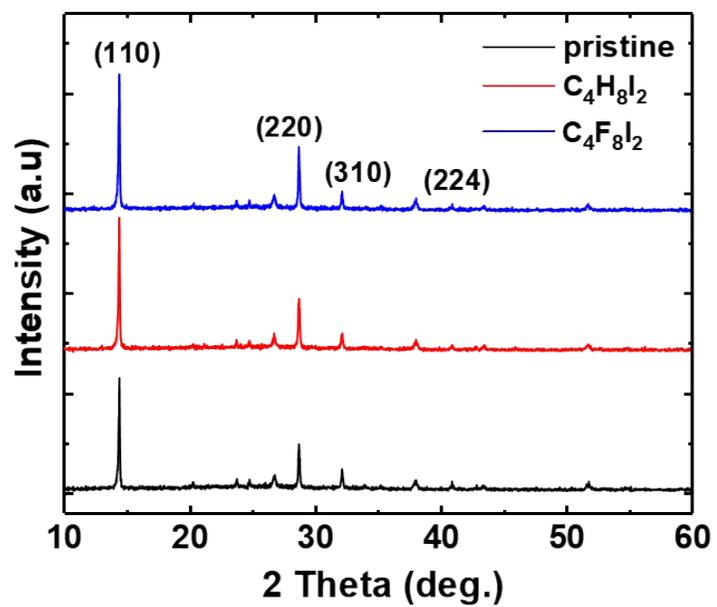


Figure S5. XRD patterns of annealed perovskite films prepared with different processing conditions.

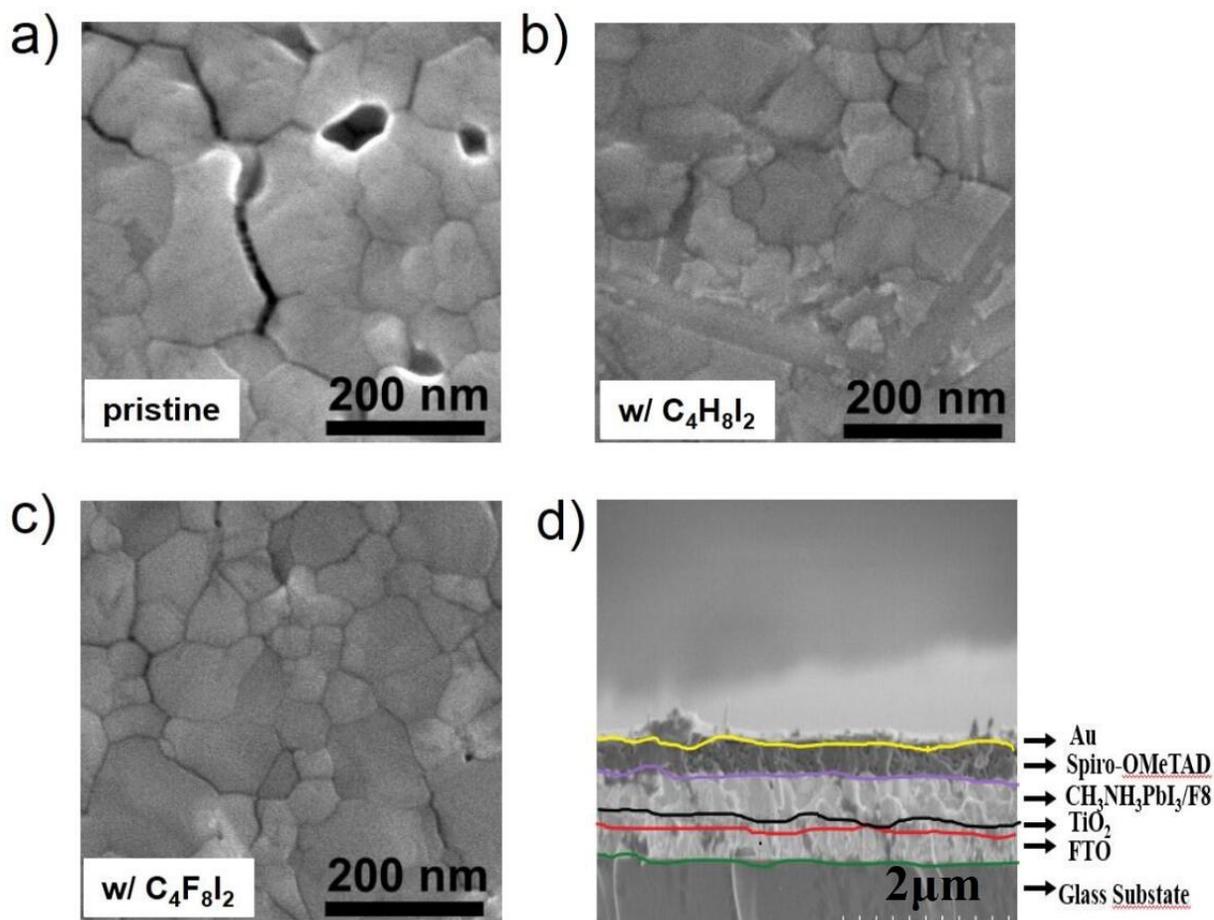


Figure S6. (a-c) Top-view scanning electron microscopic (SEM) images of as-spun films of $\text{CH}_3\text{NH}_3\text{PbI}_3$ without (a) and with $\text{C}_4\text{H}_8\text{I}_2$ (b) and $\text{C}_4\text{F}_8\text{I}_2$ (c) additives, (d) SEM cross section of our solar cell structure.

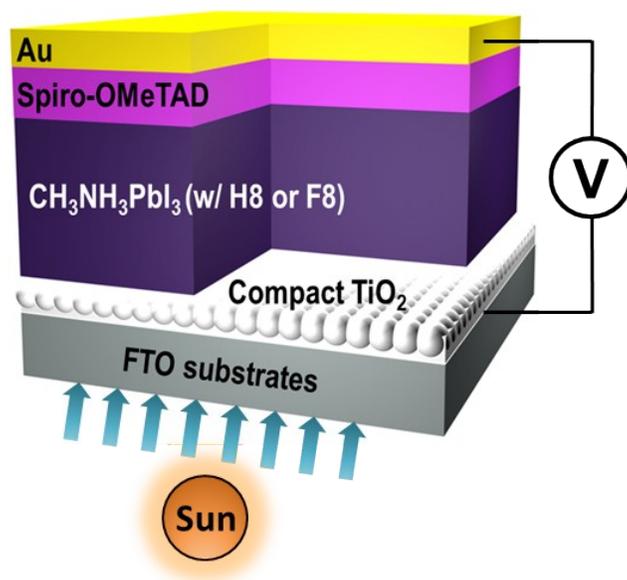


Figure S7. Sketched planar device architecture of CH₃NH₃PbI₃ solar cells based on FTO/compact TiO₂ cathode.

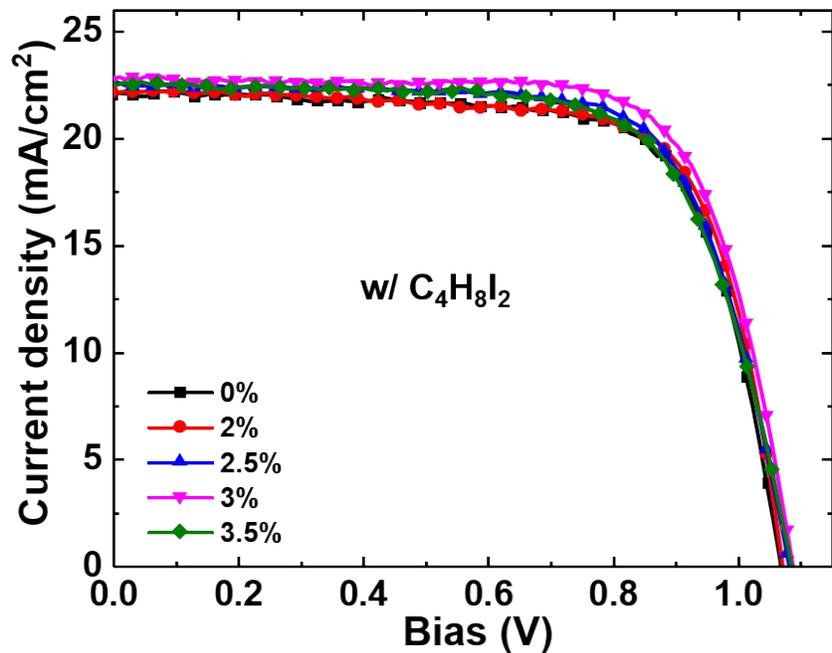


Figure S8. Current density versus voltage (J - V) characteristics of CH₃NH₃PbI₃ solar cells processed with different concentrations of C₄H₈I₂ additives (vol. ratio) in the reverse scan direction.

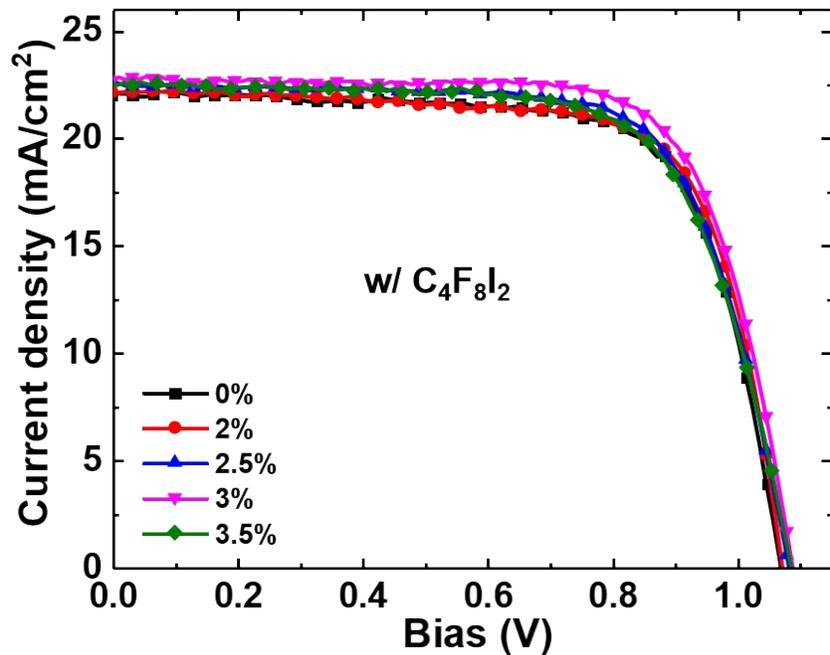


Figure S9. *J-V* characteristics of CH₃NH₃PbI₃ solar cells processed with various concentrations of C₄F₈I₂ additives in the reverse scan.

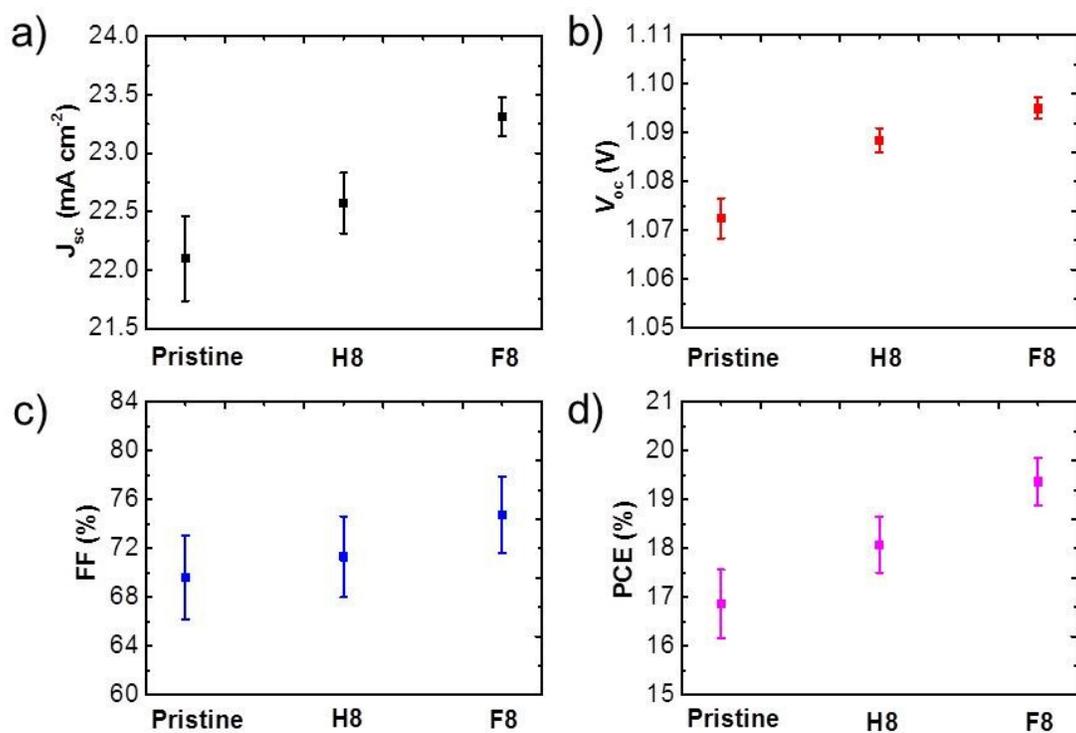


Figure S10. Averaged (a) J_{sc} , (b) V_{oc} , (c) FF, and (d) PCE of $\text{CH}_3\text{NH}_3\text{PbI}_3$ solar cells based on 20 devices in each condition. Also included are the statistical deviations of respective device parameters.

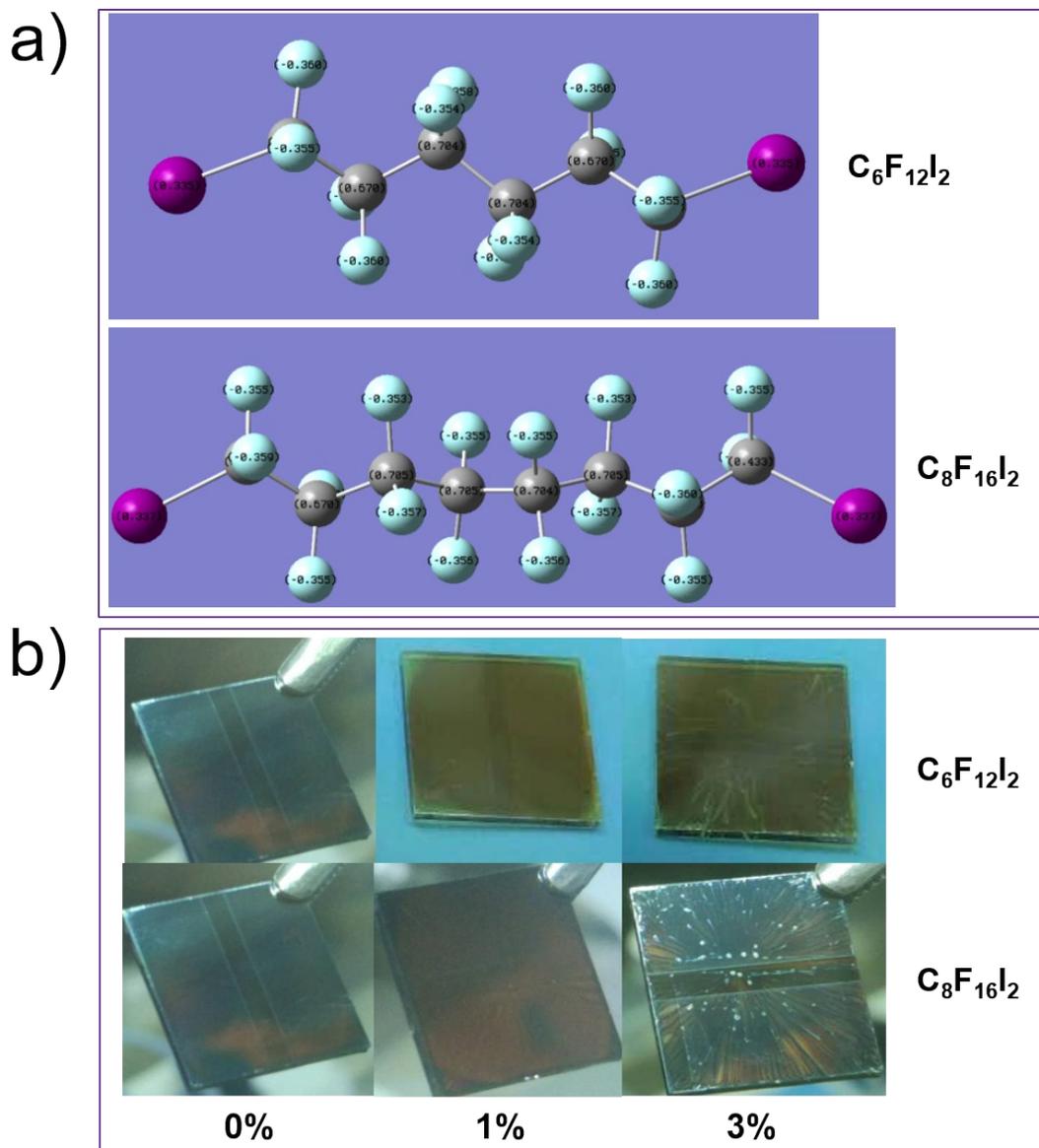


Figure S11. (a) Chemical structure of diiodoperfluoroalkyl additives of $C_6F_{12}I_2$ and $C_8F_{16}I_2$ with longer carbon chains obtained by DFT calculations together with the Mulliken charges for individual atoms. (b) Photos of the cast $CH_3NH_3PbI_3$ films processed with various concentrations of long-chain additives.

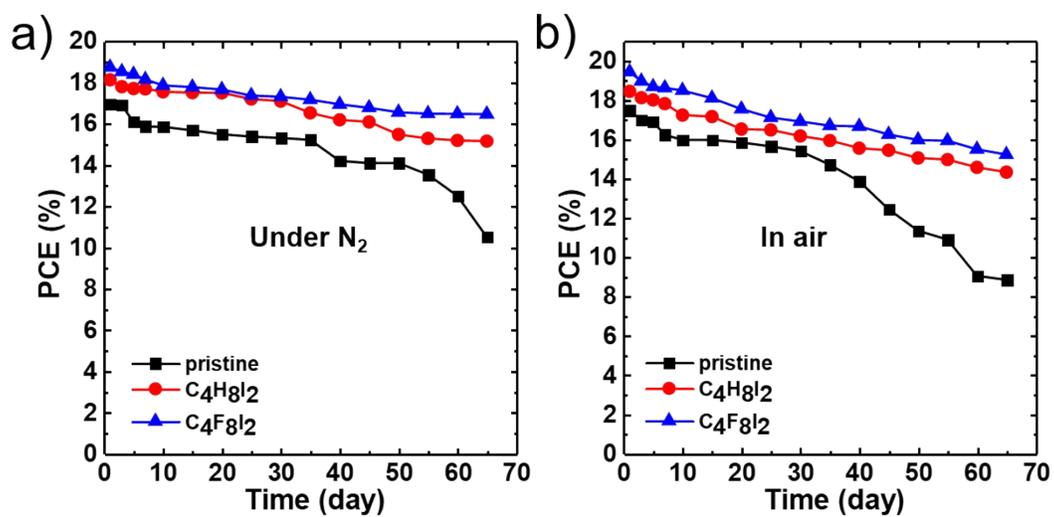


Figure S12. PCEs of various CH₃NH₃PbI₃ solar cells as a function of time when kept in (a) nitrogen, and (b) ambient environment.

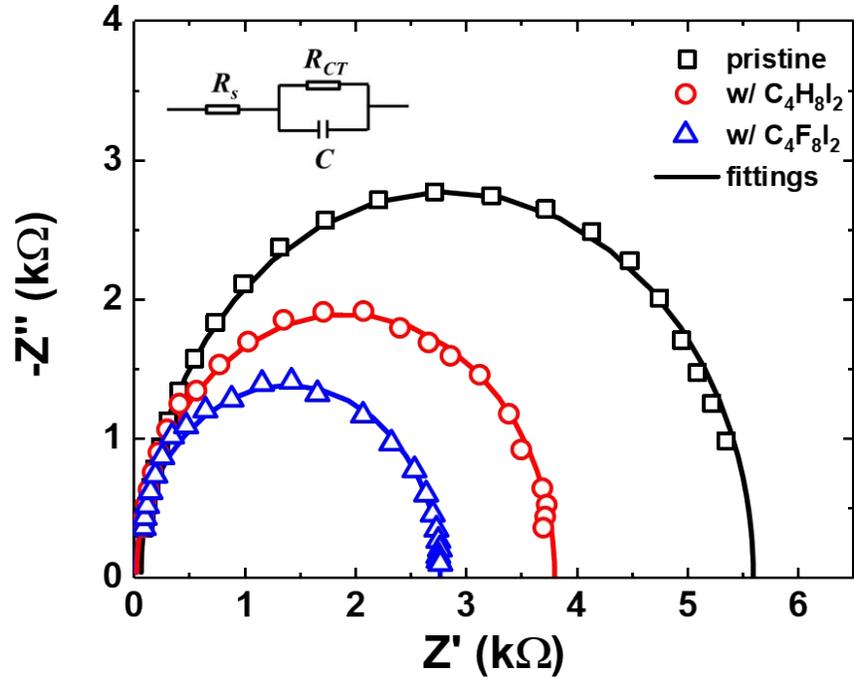


Figure S13. Nyquist plot of impedance spectroscopy measured on various CH₃NH₃PbI₃ solar cells at 100 mW/cm² irradiation (bias = 0 V). Inset: equivalent circuit used to fit the impedance spectra.

Table S1. XPS peak percentage and ratio of core level I 3d and Pb 4f of various CH₃NH₃PbI₃ films.

Element	pristine	w/ C ₄ H ₈ I ₂	w/ C ₄ F ₈ I ₂
I 3d	38.795 %	35.419 %	46.737 %
Pb 4f	14.737 %	11.318 %	15.812 %
I/Pb ratio	2.63:1	3.13:1	2.95:1

Table S2. Time constants related to the fast (τ_1) and slow (τ_2) decays extracted from time-resolved PL spectroscopy of CH₃NH₃PbI₃ films.

	τ_1 (ns)	τ_2 (ns)
pristine	23.92	66.59
C ₄ H ₈ I ₂ (3%)	25.46	68.74
C ₄ F ₈ I ₂ (3%)	28.16	74.85

Table S3. CH₃NH₃PbI₃ solar cell parameters (best) processed with different concentrations of C₄H₈I₂ additives in the reverse scan direction.

	V_{oc} (V)	J_{sc} (mA/cm ²)	FF (%)	PCE (%)
0	1.07	22.09	71.87	16.97
2.0%	1.07	22.14	72.86	17.24
2.5%	1.08	22.57	71.25	17.37
3.0%	1.09	22.85	73.32	18.08
3.5%	1.08	22.47	70.12	17.04

Table S4. CH₃NH₃PbI₃ solar cell parameters (best) processed with different concentrations of C₄F₈I₂ additives in the reverse scan direction.

	<i>V</i>_{oc} (V)	<i>J</i>_{sc} (mA/cm²)	FF (%)	PCE (%)
0	1.07	22.09	71.87	16.97
2.0%	1.09	22.37	70.65	17.31
2.5%	1.09	22.84	73.32	18.09
3.0%	1.10	23.31	74.78	19.17
3.5%	1.09	22.88	70.72	17.72

Table S5. CH₃NH₃PbI₃ solar cell parameters (best) processed with different concentrations of C₆F₁₂I₂ additives in the reverse scan direction.

	<i>V</i>_{oc} (V)	<i>J</i>_{sc} (mA/cm²)	FF (%)	PCE (%)
0	1.07	22.09	71.87	16.97
1.0%	0.99	18.88	48.47	9.1
3.0%	1.05	20.13	51.65	10.9
5.0%	1.06	19.07	47.58	9.6
7.0%	1.05	18.07	45.87	8.7

Table S6. CH₃NH₃PbI₃ solar cell parameters (best) processed with different concentrations of C₈F₁₆I₂ additives in the reverse scan direction.

	V_{oc} (V)	J_{sc} (mA/cm ²)	FF (%)	PCE (%)
0	1.07	22.09	71.87	16.97
1.0%	1.06	19.46	71.83	14.92
3.0%	1.04	18.18	66.16	12.46

Table S7. Device parameters of CH₃NH₃PbI₃ solar cell parameters extracted in the forward (F) and reverse (R) scan directions together with the calculated hysteresis index (HI).

	V_{oc} (V)	J_{sc} (mA/cm ²)	FF (%)	PCE (%)	HI
control-F	1.08	22.44	63.08	15.29	0.224
control-R	1.08	22.45	71.95	17.46	
w/ C ₄ H ₈ I ₂ -F	1.09	22.38	70.34	17.17	0.055
w/ C ₄ H ₈ I ₂ -R	1.09	22.62	75.03	18.52	
w/ C ₄ F ₈ I ₂ -F	1.09	23.21	73.07	18.49	0.050
w/ C ₄ F ₈ I ₂ -R	1.09	23.57	78.18	20.12	

Table S8. Parameters extracted from the the impedance spectroscopy measured on various CH₃NH₃PbI₃ solar cells under 100 mW/cm² irradiation (bias = 0 V).

	pristine	w/ C ₄ H ₈ I ₂	w/ C ₄ F ₈ I ₂
R_s (Ω)	63.53	29.57	18.35
R_{CT} (Ω)	5540	3782	2757
C_n (nF)	5.26	5.45	5.47